

A Fully Digital Approach to Sub-Micron Resolution Particle Detection: The Particam Concept

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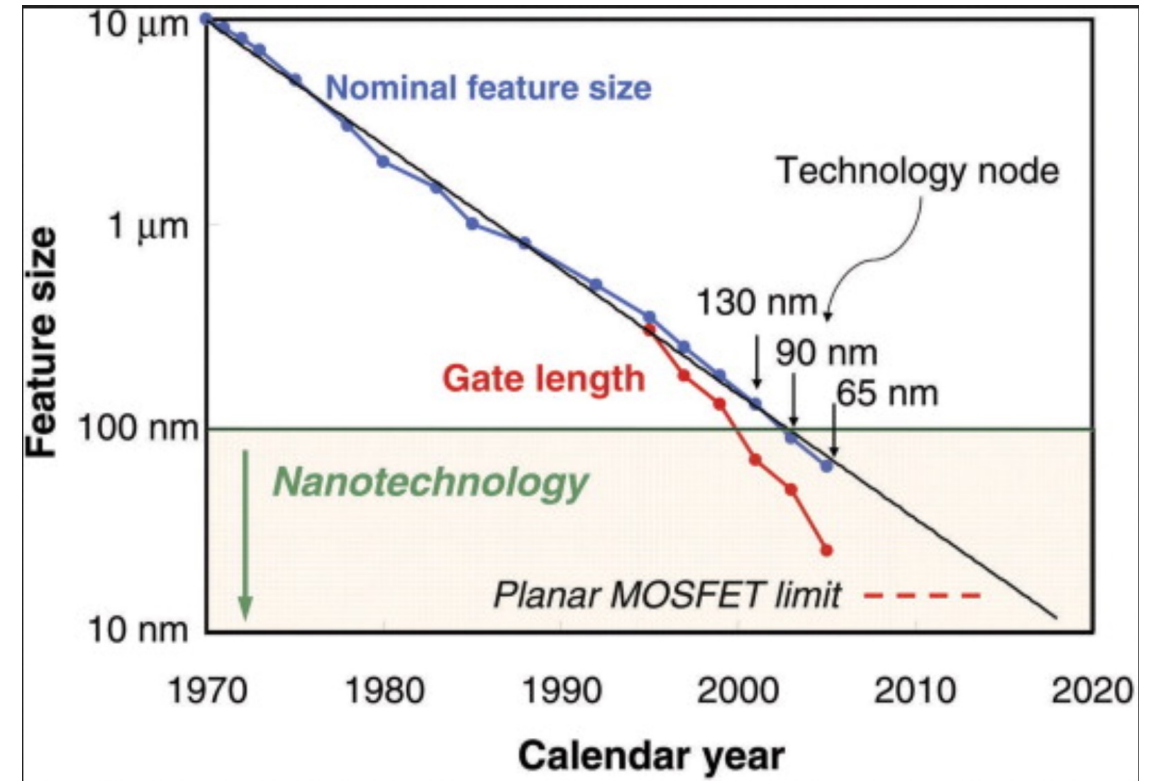
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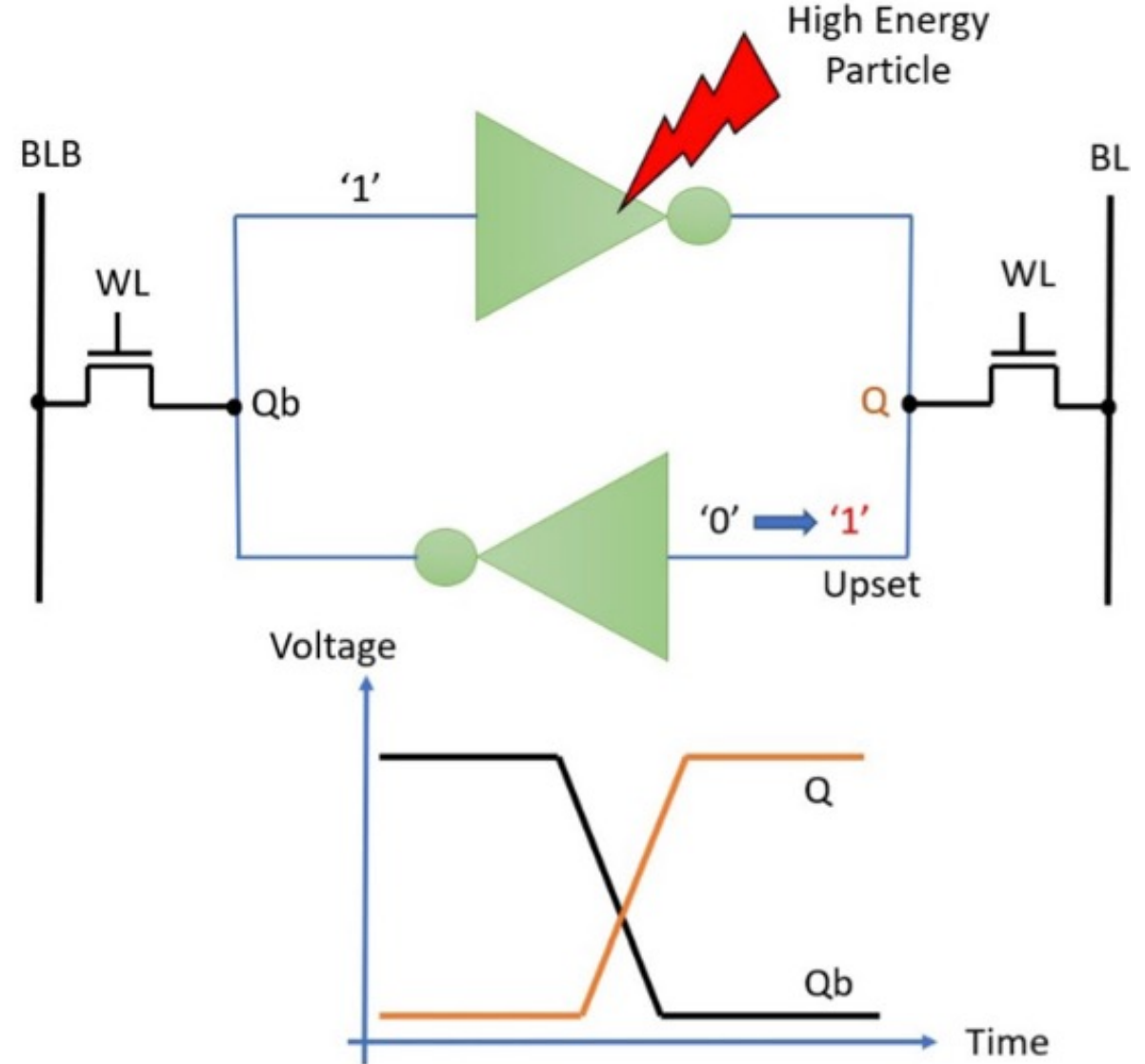
Introduction

- The transition to smaller silicon feature sizes in particle physics has slowed down in recent years.
- Design becomes much more expensive and complex.
- Limitations due to bump bonds and transistor size for analogue circuits.
- A new approach is needed to achieve a sub-micron spatial resolution.

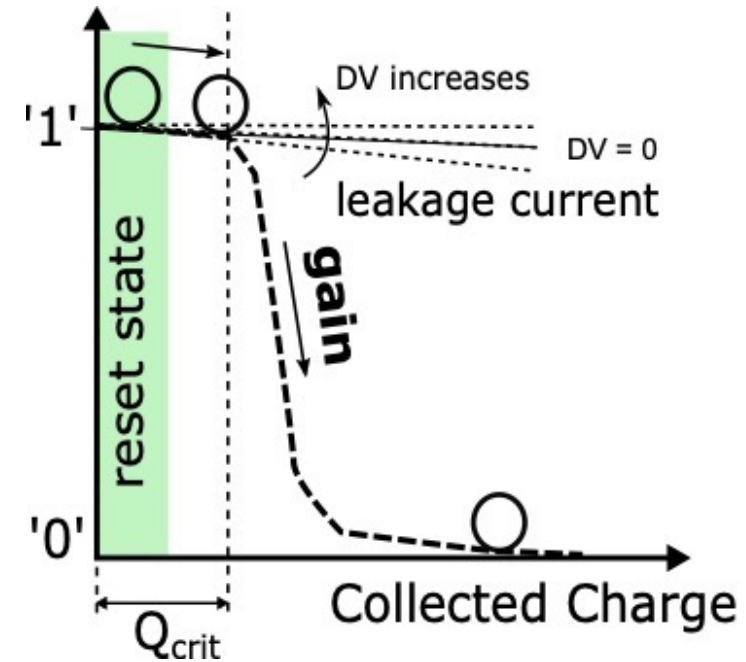
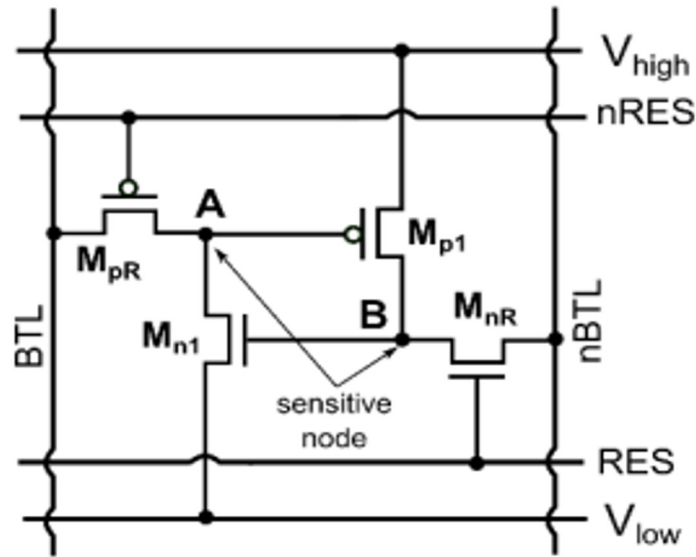


Particam Concept

- Uses the idea of Single Event Upset (SEU).
- Presence of particles may induce a flip of the memory content.
- A minimum charge (Q_{crit}) that forces the change in memory state.

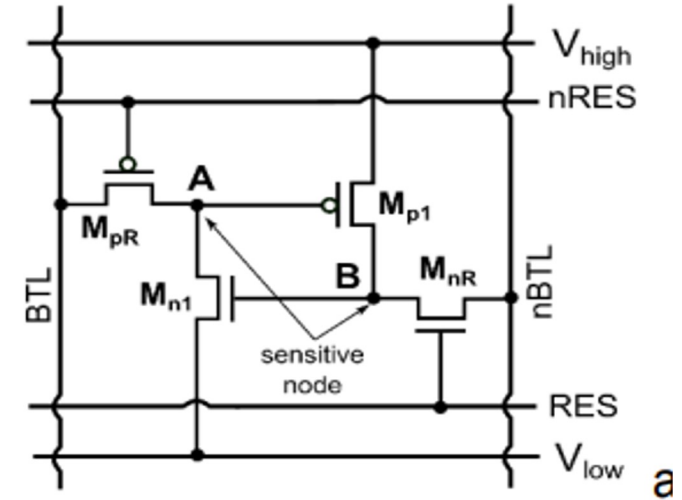
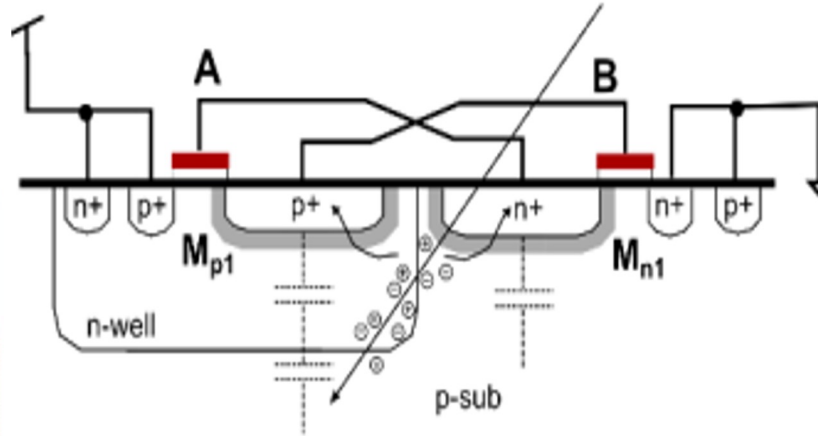
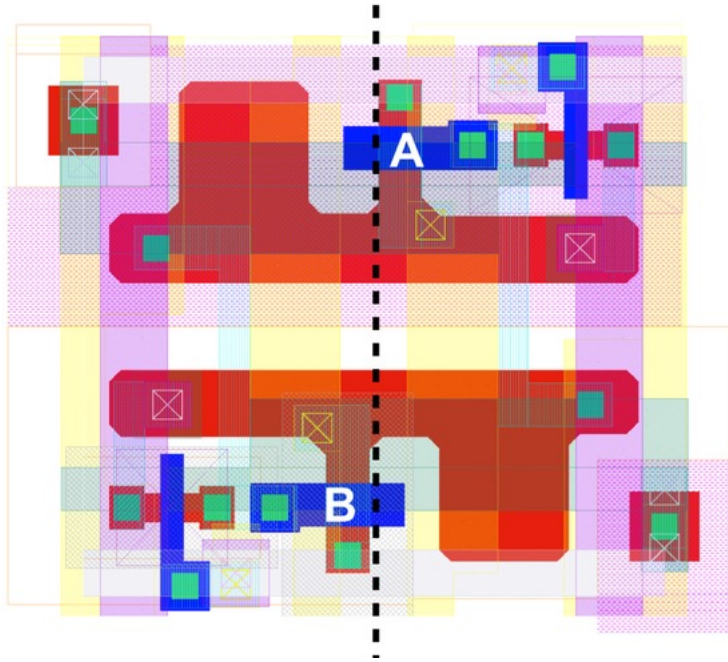


Particam Concept



- This has four transistors: M_{n1} and M_{p1} (memory block) and M_{nR} and M_{pR} (for reset and read).
- During reset phase nodes A and B are pre-charged to V_{dd} and gnd respectively through the bitline then left floating.
- ISSUE: Leakage current on nodes A and B can change the memory state even if there is no particle (false event)
- → Periodic reset needed.

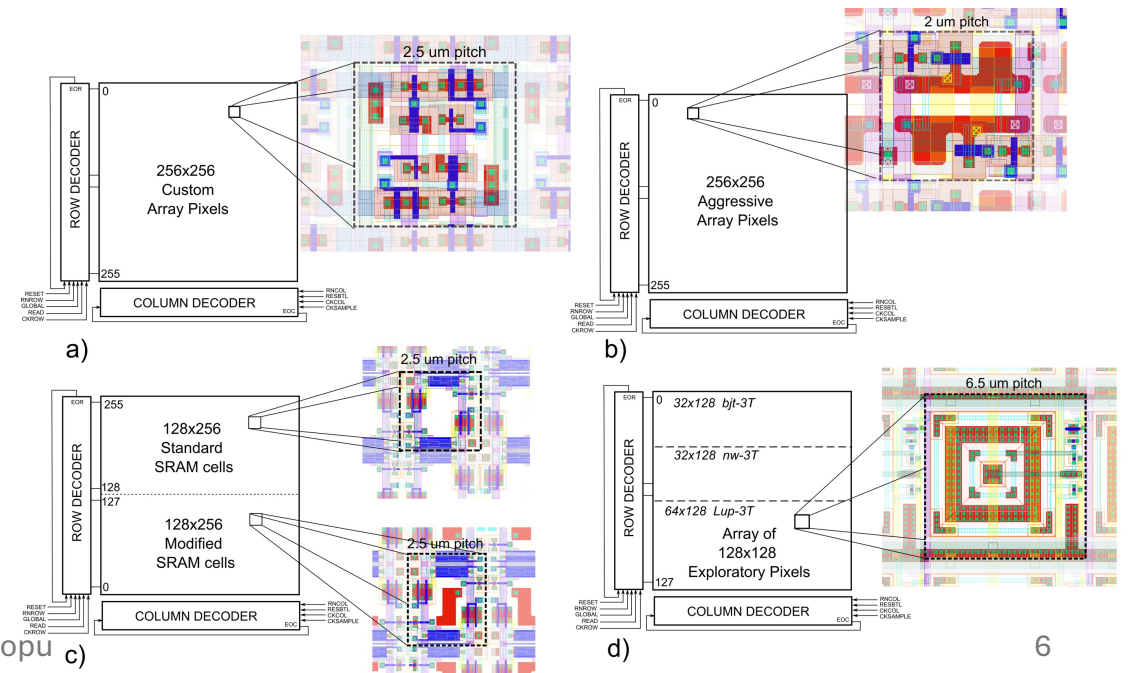
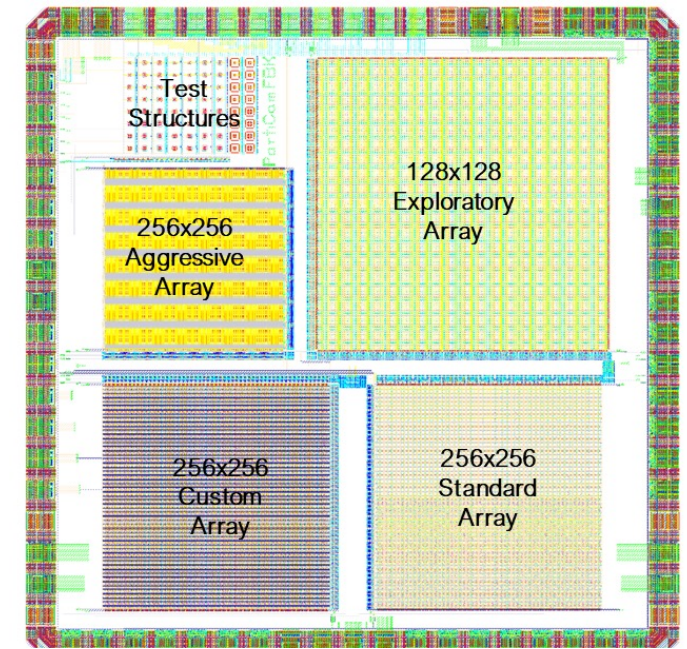
Particam Implementation

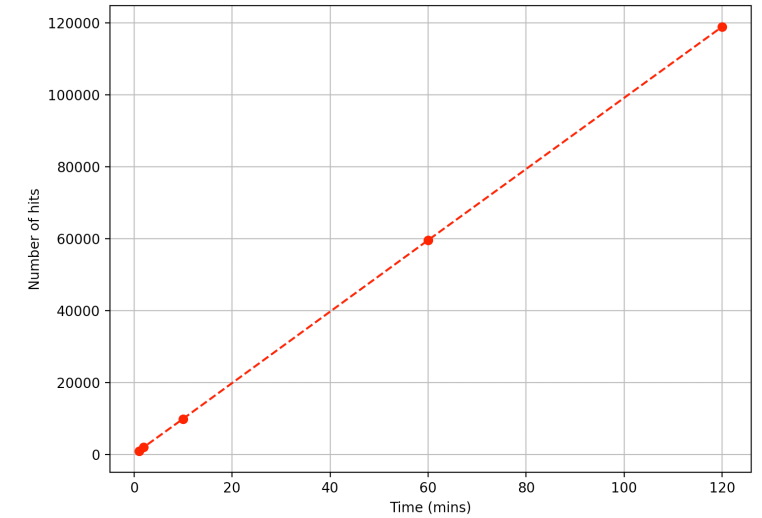
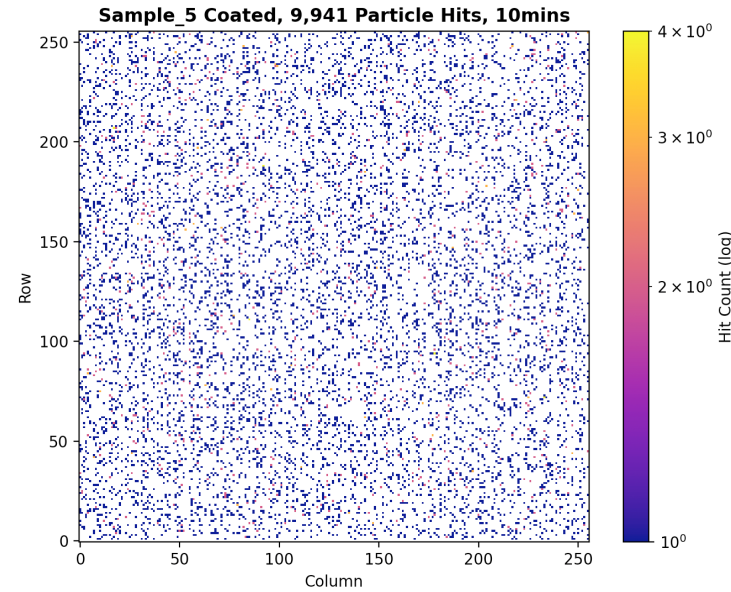
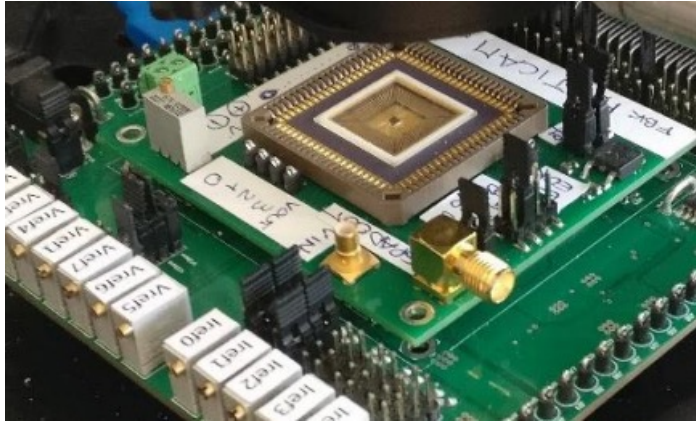


- The cell value is then readout by a column level sensor circuit.
- Enlarged junction for more charge collection.

Particam Prototype

- Designed by FBK.
- Realized in UMC 65nm low leakage technology and contains four arrays.
- Many different RAM cell designs.
 1. **Standard array:** 256x256 pixels consisting of standard SRAM with 2.5 μm pitch.
 2. **Custom array:** 256x256 pixels consisting of a novel with 2.5 μm pitch.
 3. **Aggressive array:** 256x256 pixels consisting of a novel circuit with 2 μm pitch.
 4. **Exploratory array:** 128x128 pixels based on different deeper junctions with 6.5 μm pitch.
- The chip can work in global or rolling shutter mode.
- Row and Column registers able to select each element of the array (for reading or reset specific row).



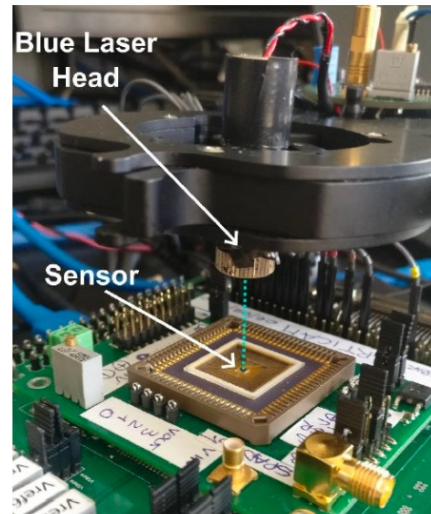


Response to α -particles

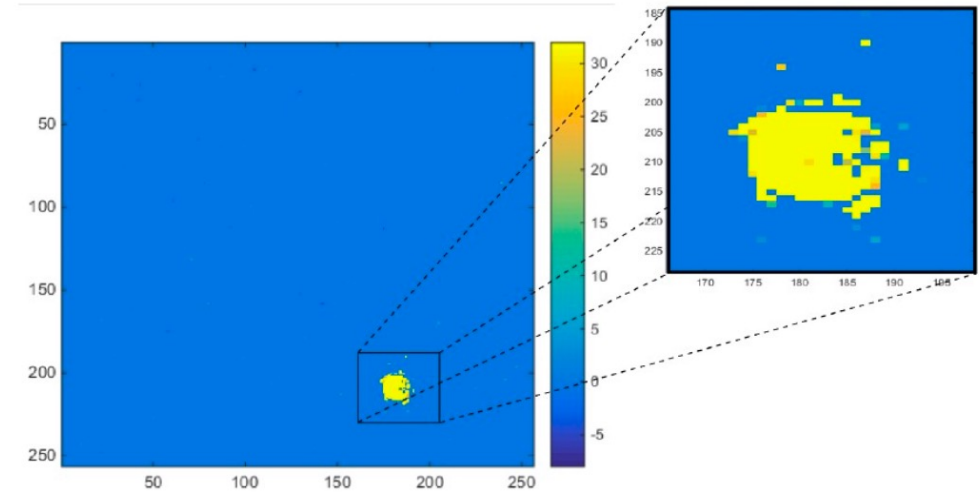
- Measurements performed by placing the Alpha source above the sensor.
- Hit number recorded for different exposure times and supply voltages.
- Very low Alpha particle detection efficiency.

Sensor Investigation

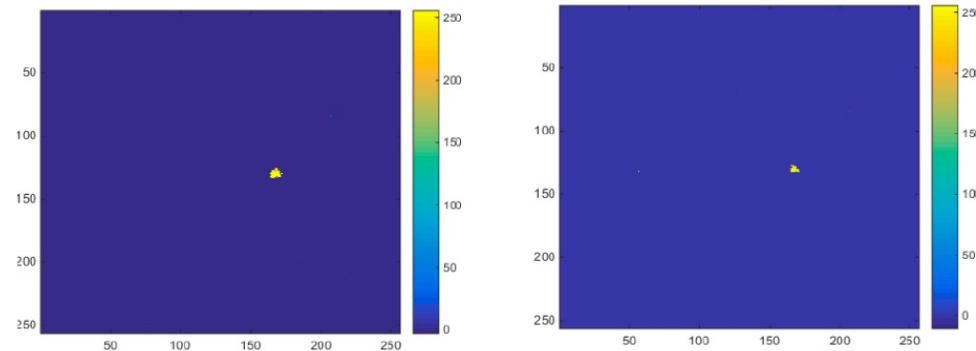
- Very low alpha particle detection efficiency
- Zero efficiency for other charged particles.
- Laser source investigation.
- *Useful as a laser sensor?!*



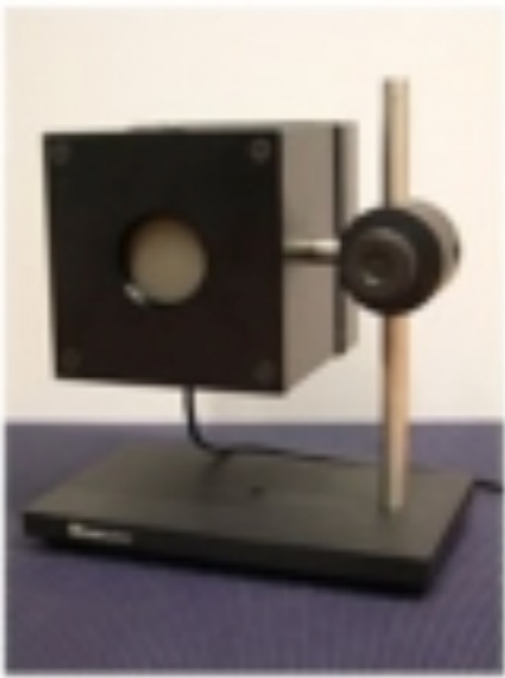
a)



b)



c)



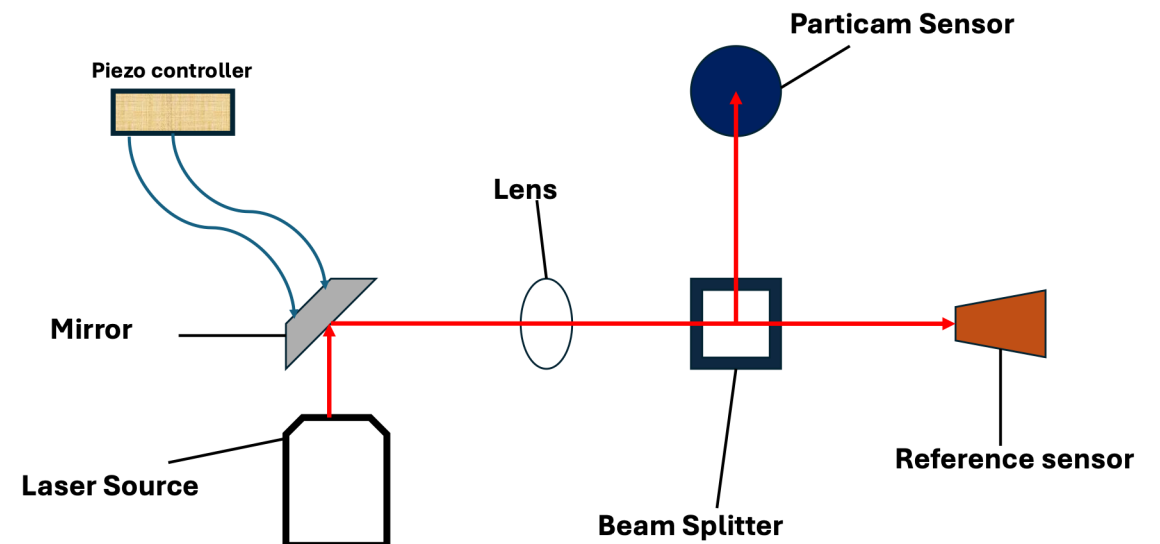
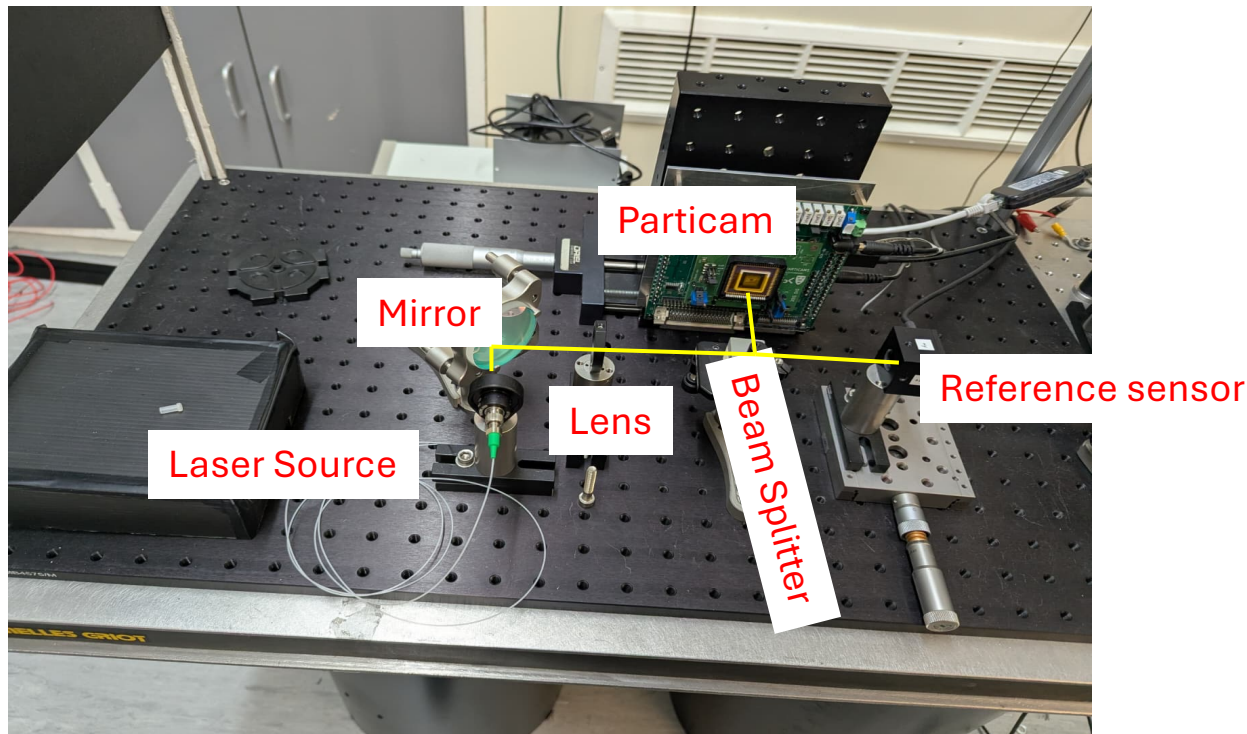
Laser Application

- Most sensors are analogue/semi-analogue.
- Precision alignment with high bandwidth.
- As a feedback loop to cater for vibration stability.
- Long range optical transmission e.g in space optics.



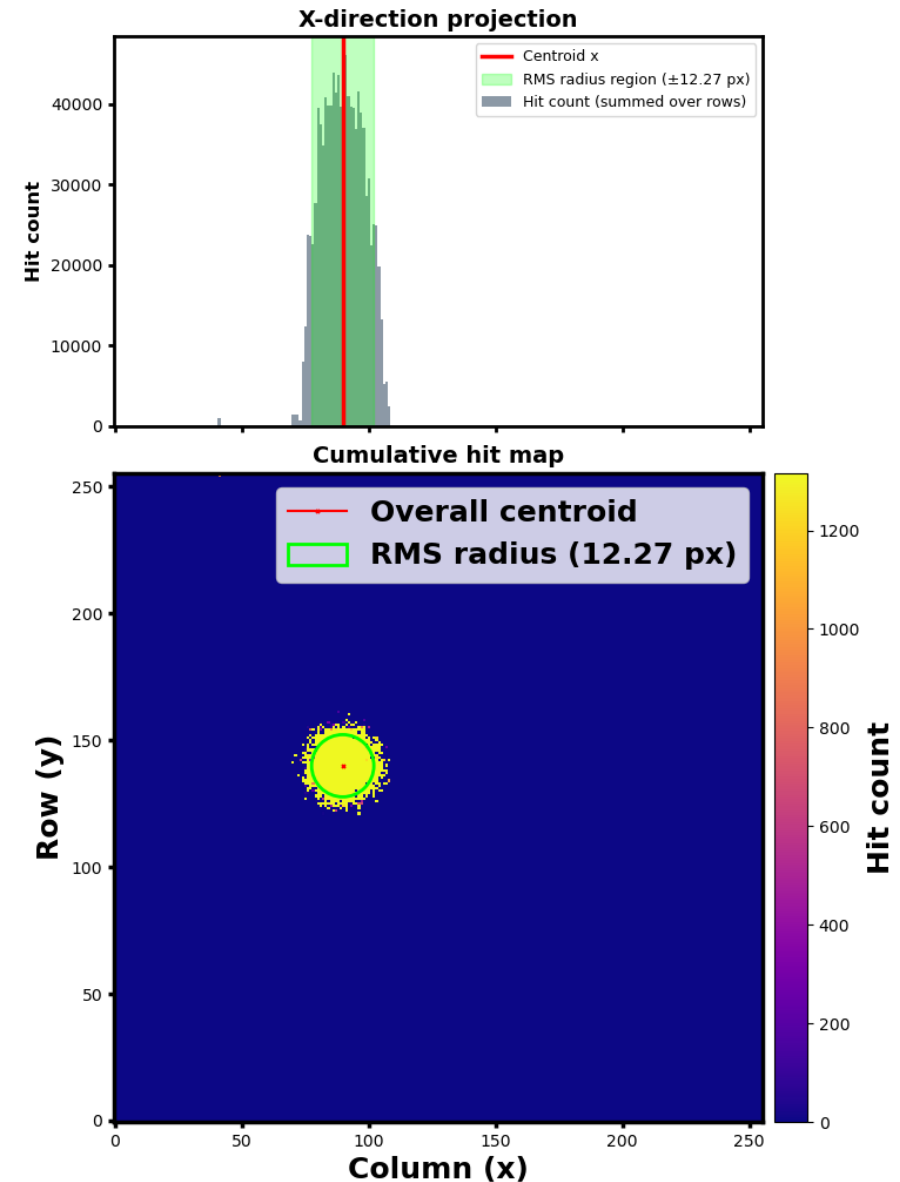
Laser Set-up

- A 780nm (infrared) continuous laser.
- OT-301 Precision position sensing amplifier.



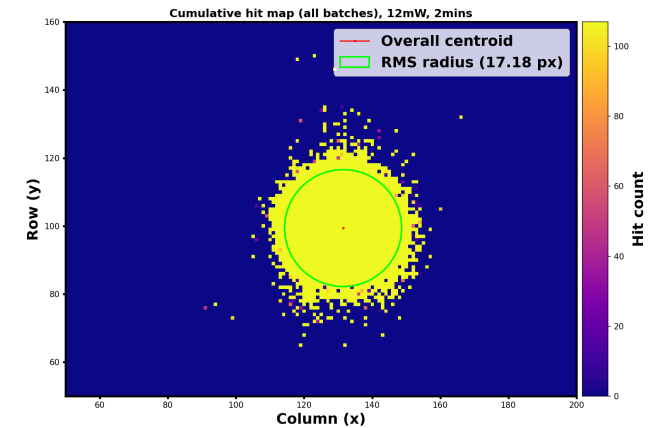
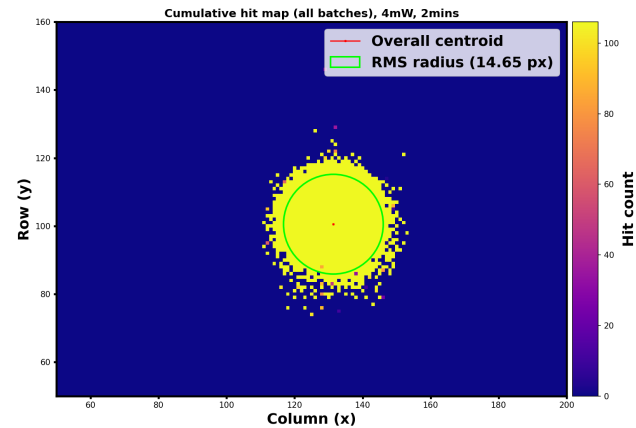
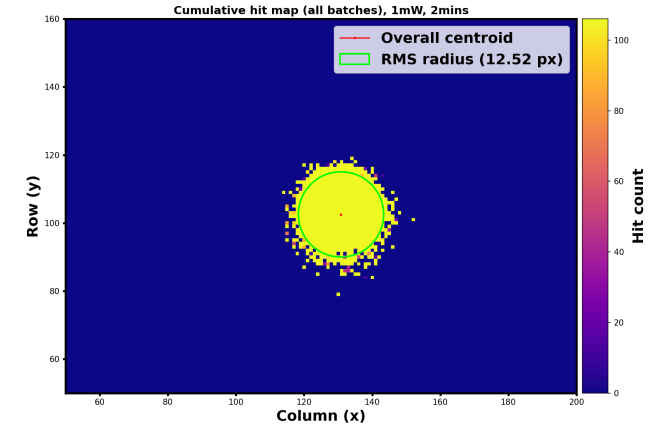
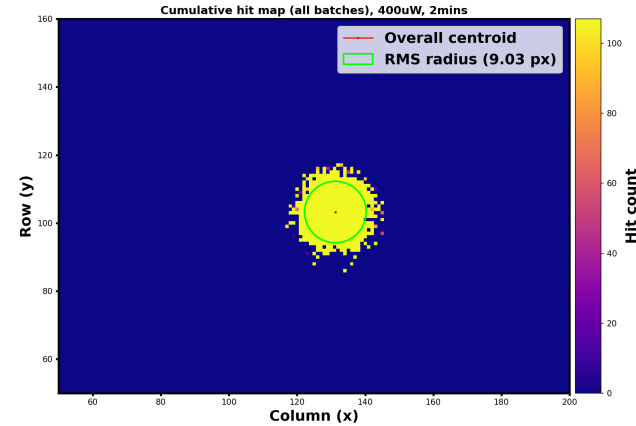
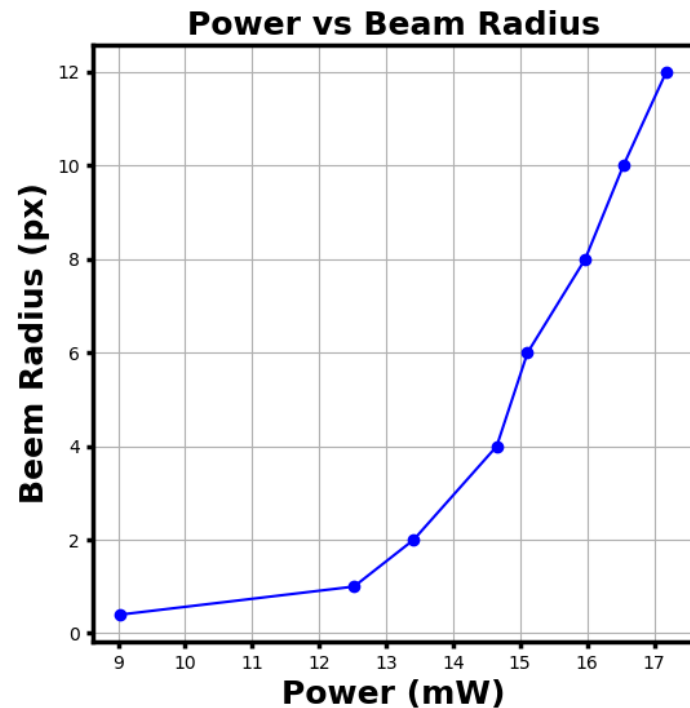
Laser Spot Centriod

- Intensity-weighted centriod of a 2D hit-count matrix.
- rms_radius: intensity-weighted RMS radius.



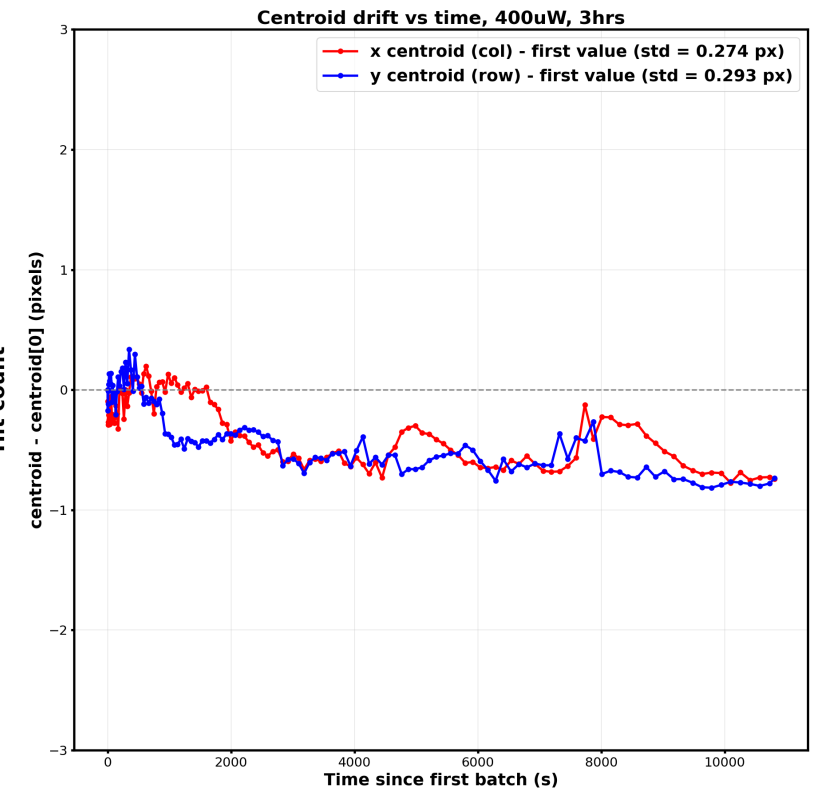
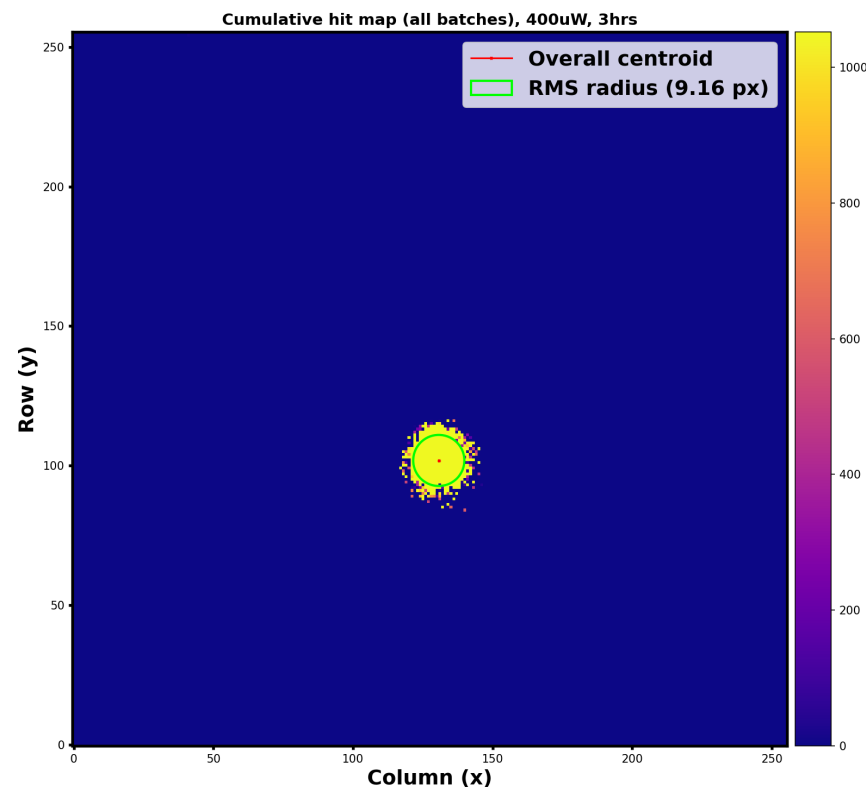
Laser Power

- Varying the laser power with a constant time.

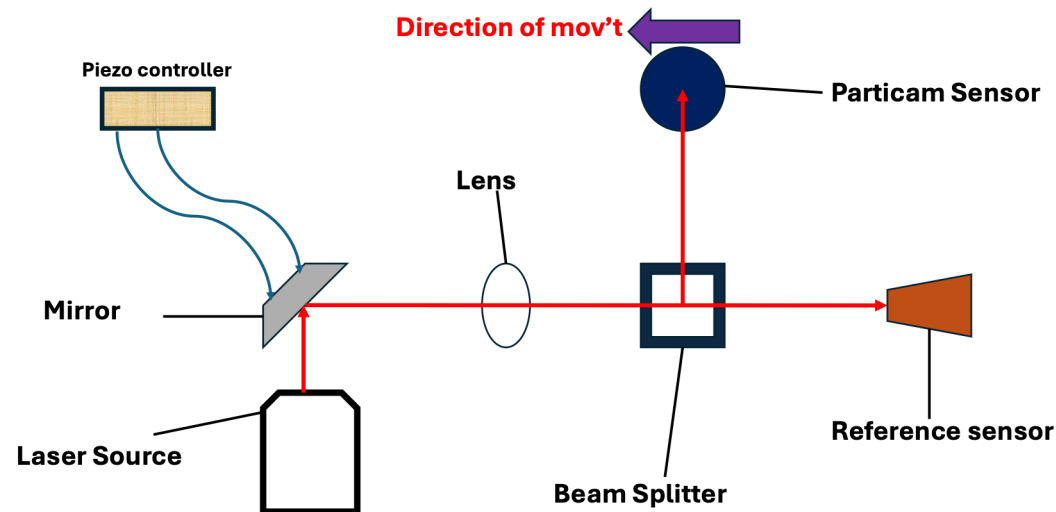


Laser Spot stability

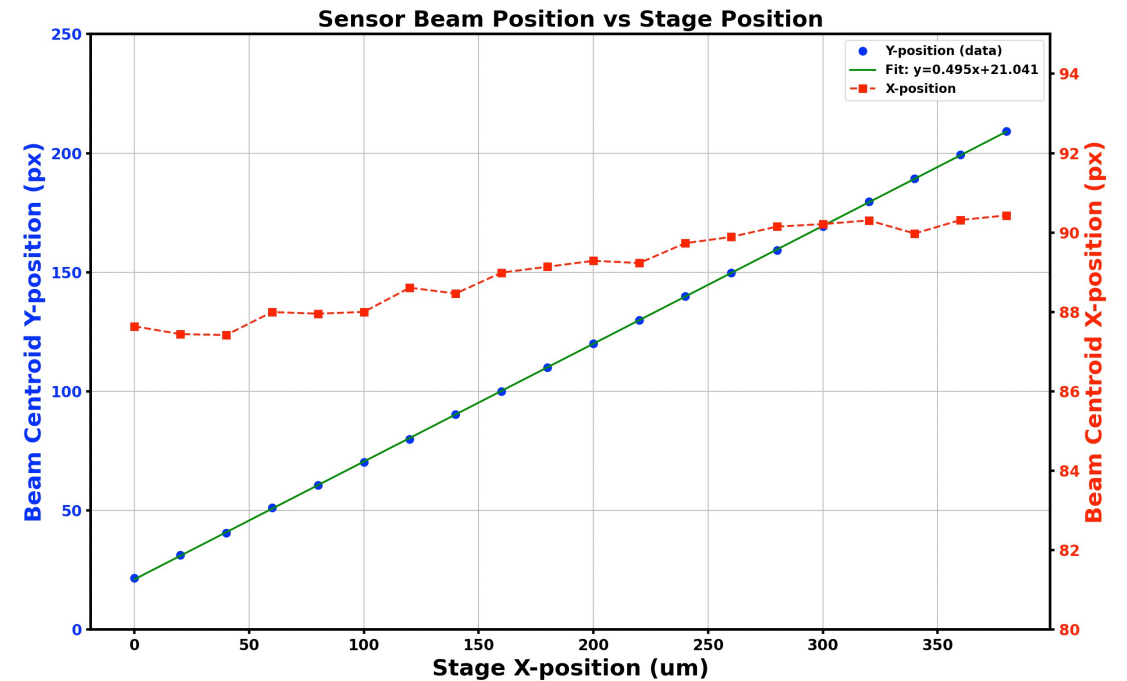
- Laser focused on the same sensor position.
- Monitor stability.
- Deviation only half a pixel = 1 μ m over 3hrs.



Particam Laser Spot Movement

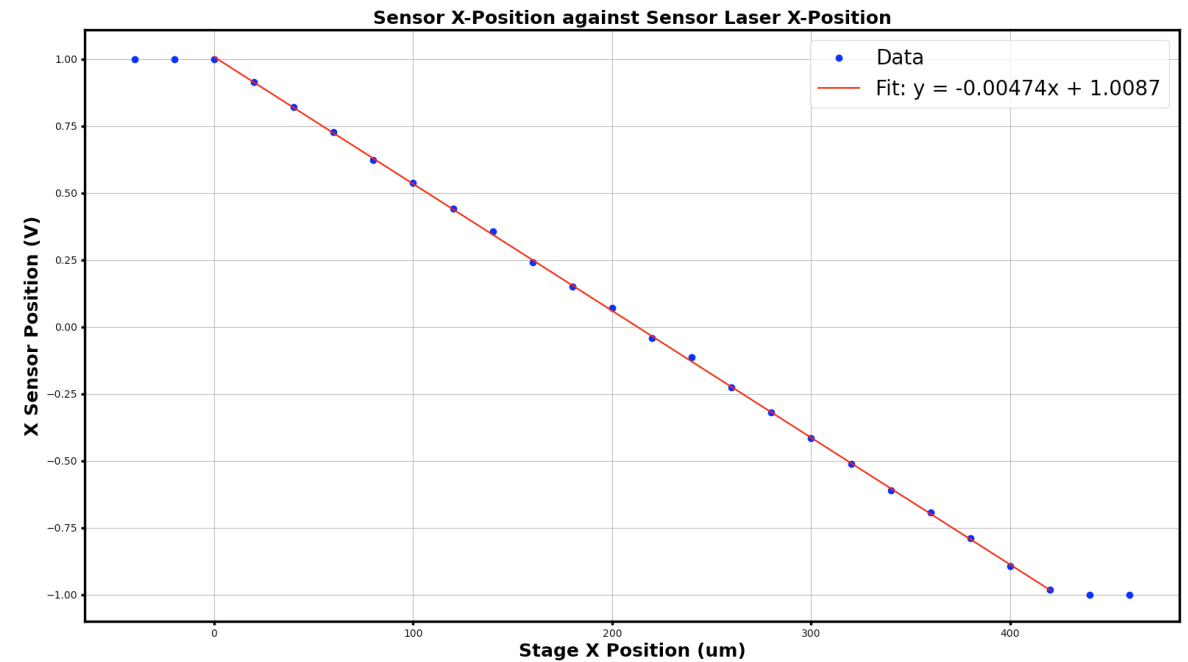
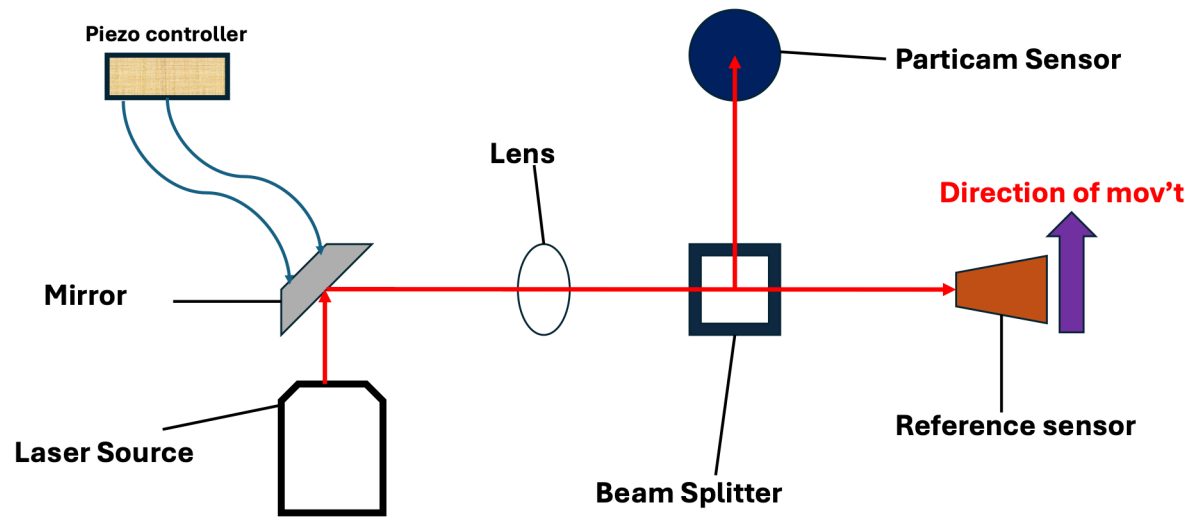


- Conversion: $1\text{ px} = 2\text{ }\mu\text{m}$
- The centroid y-position = stage x-position due to the orientation of the sensor.
- Stage step size = $10\text{ }\mu\text{m}$.
- Fit: $m = 0.495 \times 2 = 0.99$



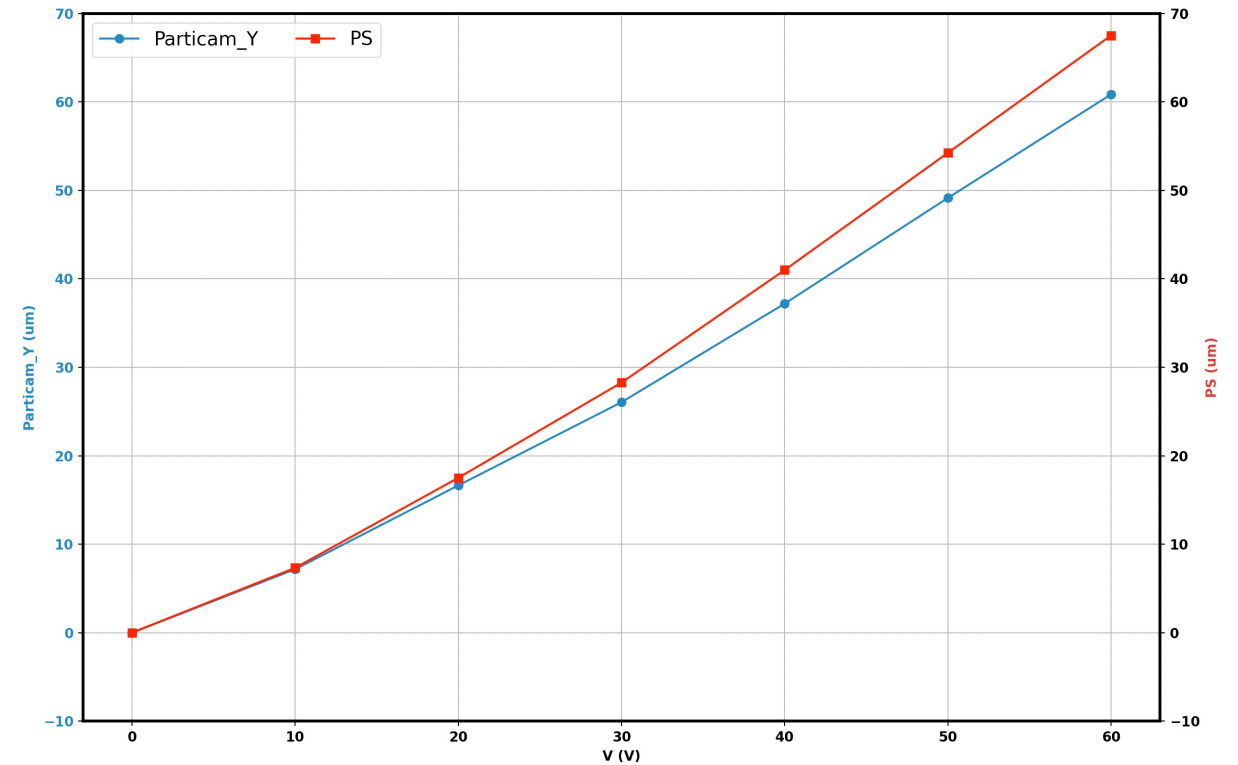
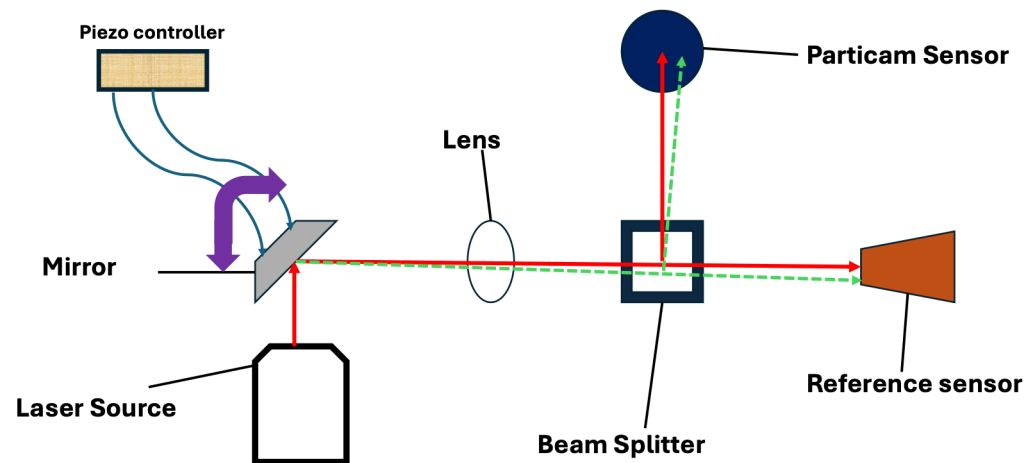
Position Sensor Laser Spot

- Step size = 20 μm (micrometer used limit).
- Position sensor (PS): 0.1 mm = 1 V.



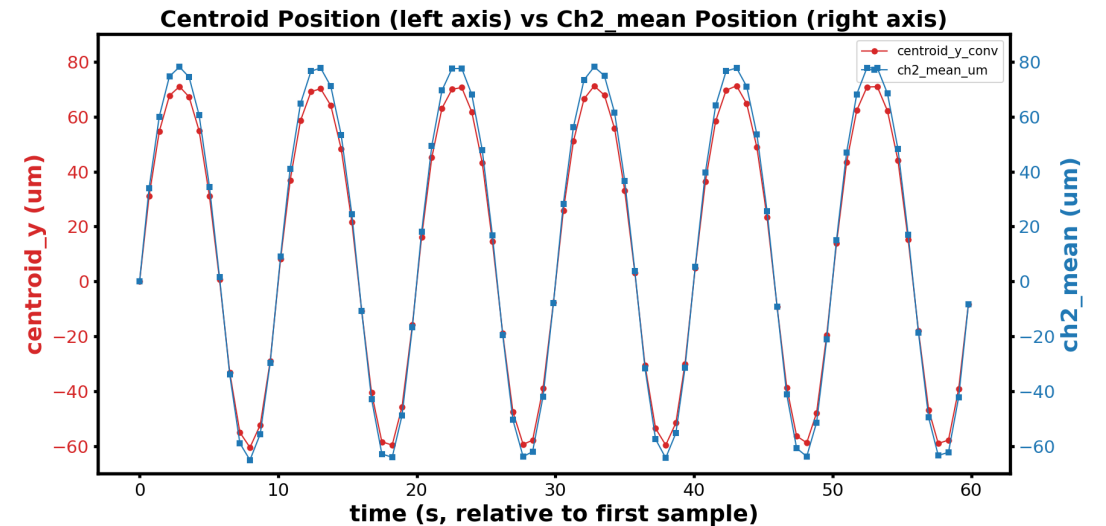
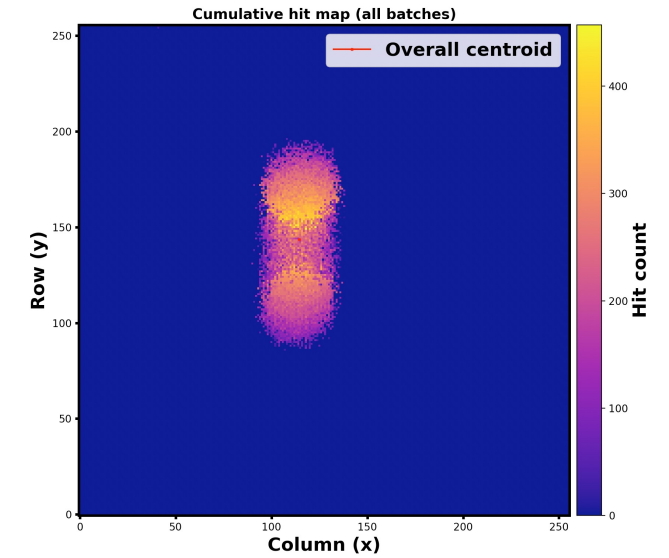
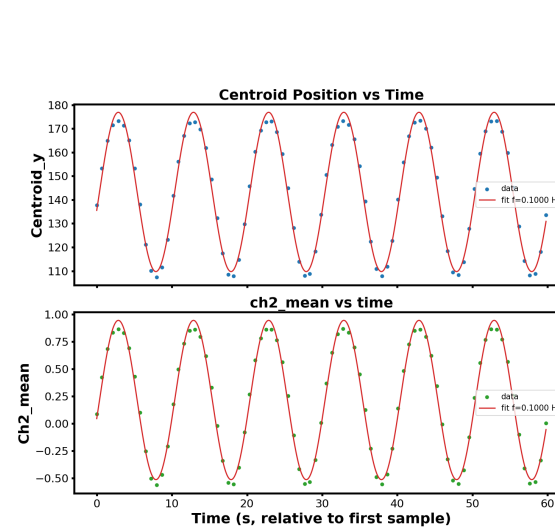
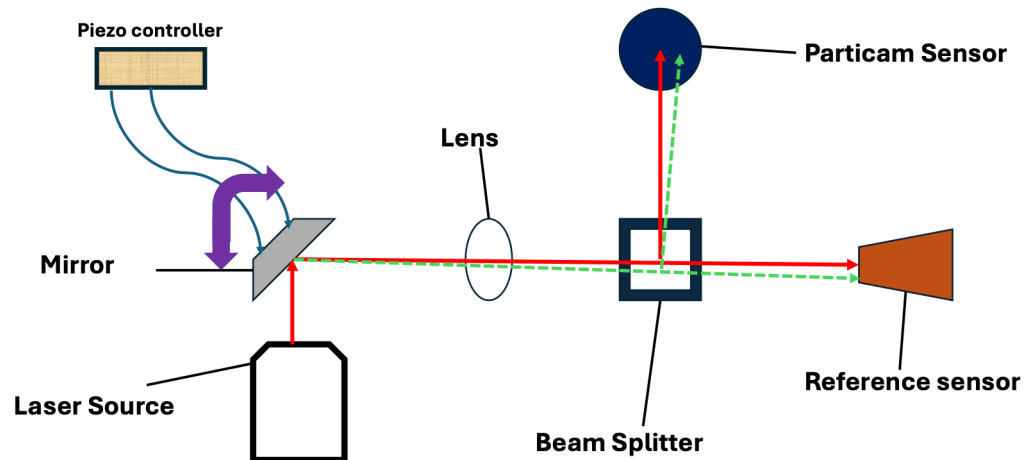
Piezo Mirror Movement

- Position sensor (PS): $0.1 \text{ mm} = 1 \text{ V}$.
- Ramped voltage from 0 to 60 V.
- Both sensors agree.



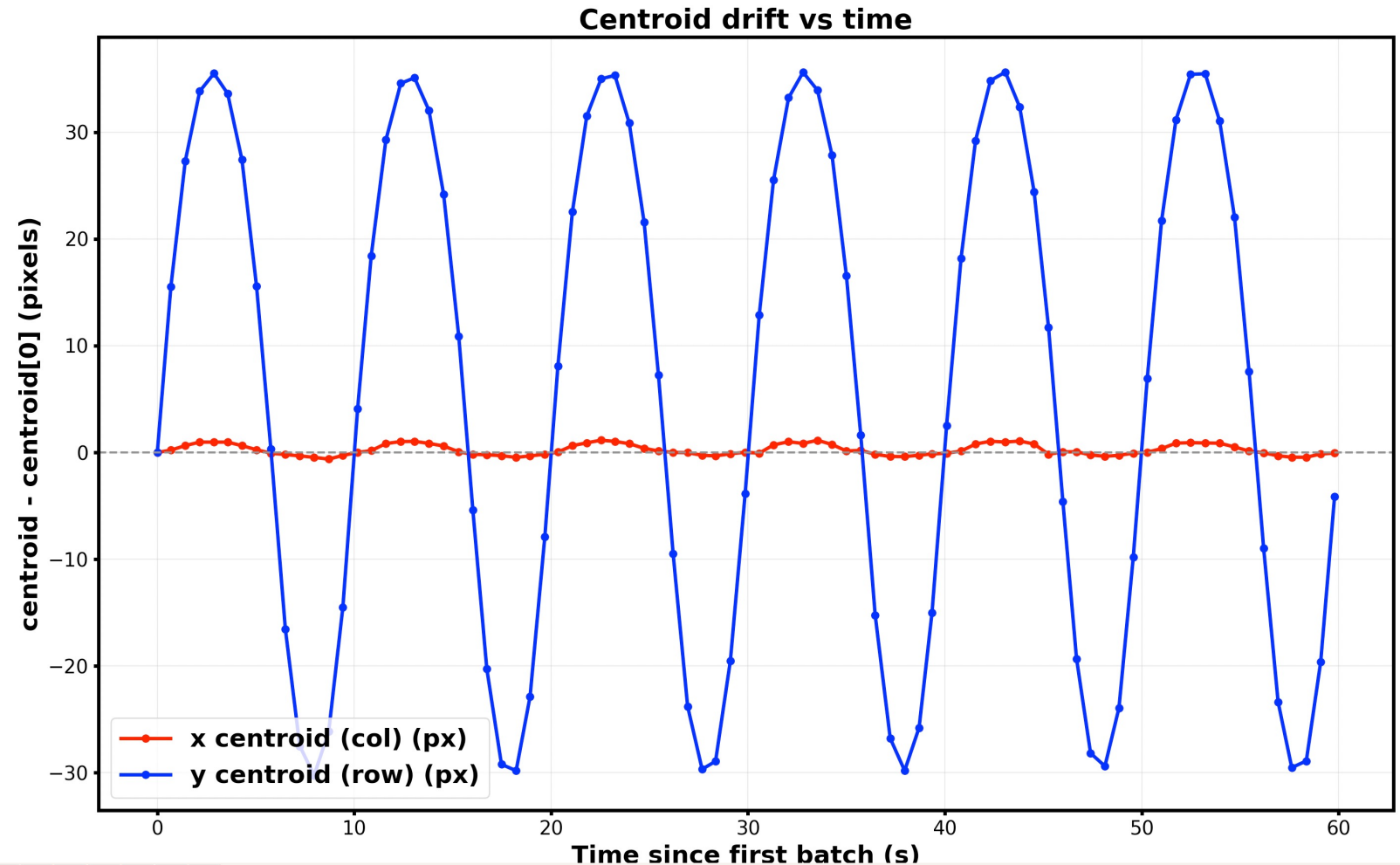
Time Dependence

- Mirror movement using a sine function.



Conclusion

- Particam was used for position sensing.
- Tested against other position sensors.
- Optimize the data acquisition process.
- Run the experiment for different frequencies.
- Submitting a new chip.



Backup

$$x_{\text{centroid}} = \frac{\sum_x \sum_y x \cdot I(x, y)}{\sum_x \sum_y I(x, y)}$$

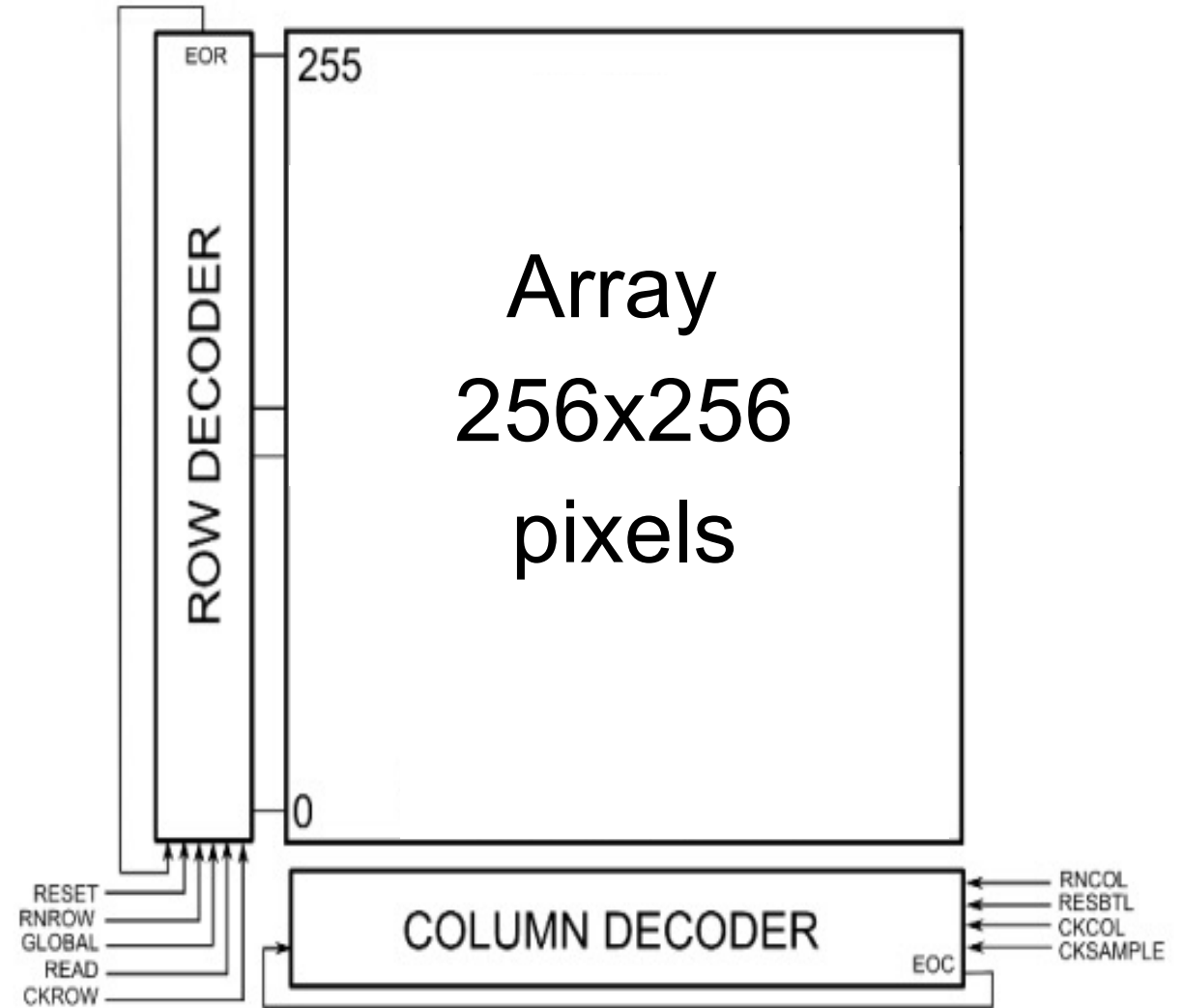
$$y_{\text{centroid}} = \frac{\sum_x \sum_y y \cdot I(x, y)}{\sum_x \sum_y I(x, y)}$$

Formula Components

- $I(x, y)$: The intensity (or hit count) at pixel coordinate (x, y) .
- **Denominator** ($\sum \sum I$): The total sum of all intensities in the matrix.
- **Numerator**: The sum of each pixel's coordinate multiplied by its intensity weight.

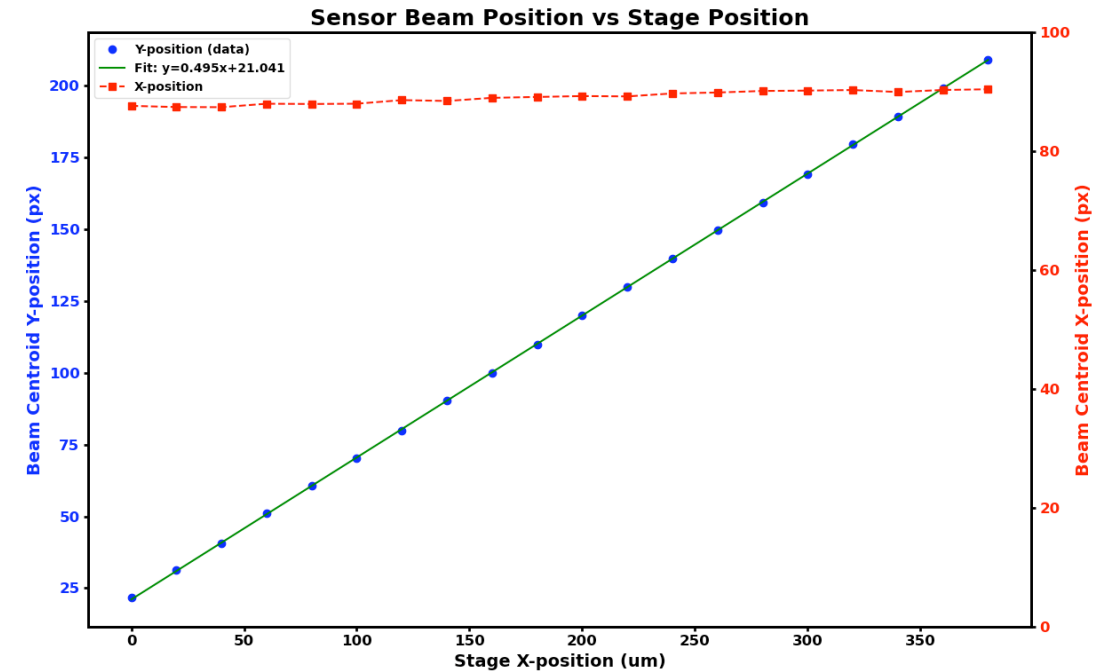
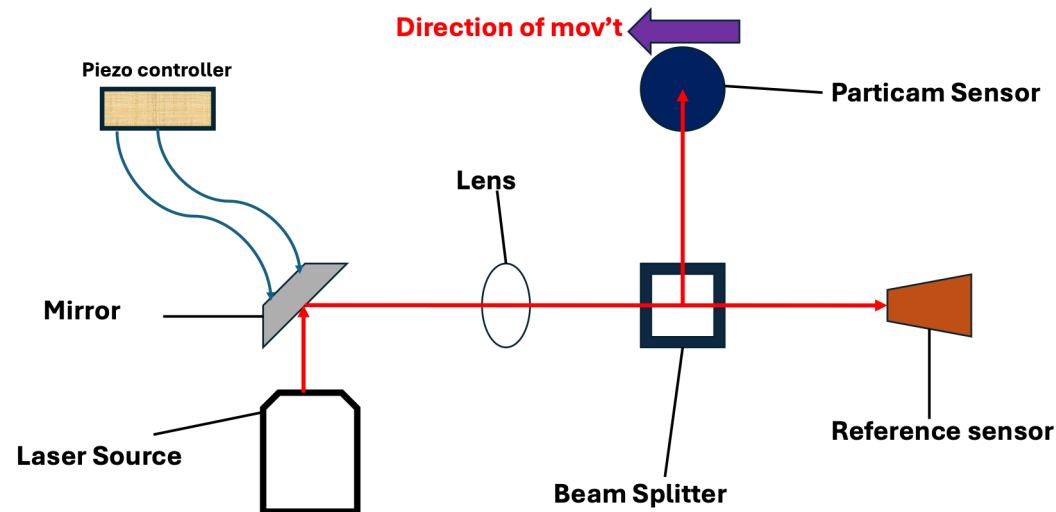
Readout

- Decoder based readout.
- Decoders implemented as circular shift registers.
- Data is connected in groups 8 columns to output pads.
- Can be operated in either global or rolling shutter.
- Exploratory array has 128×128 pixel, other arrays have 256×256 .



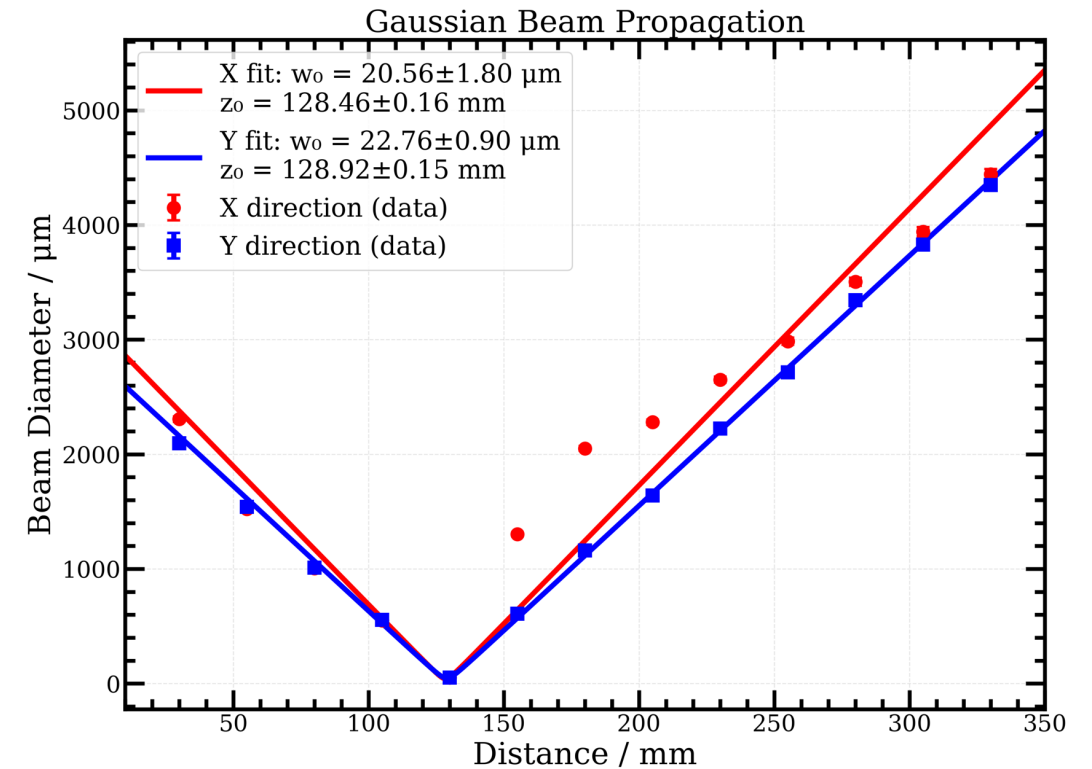
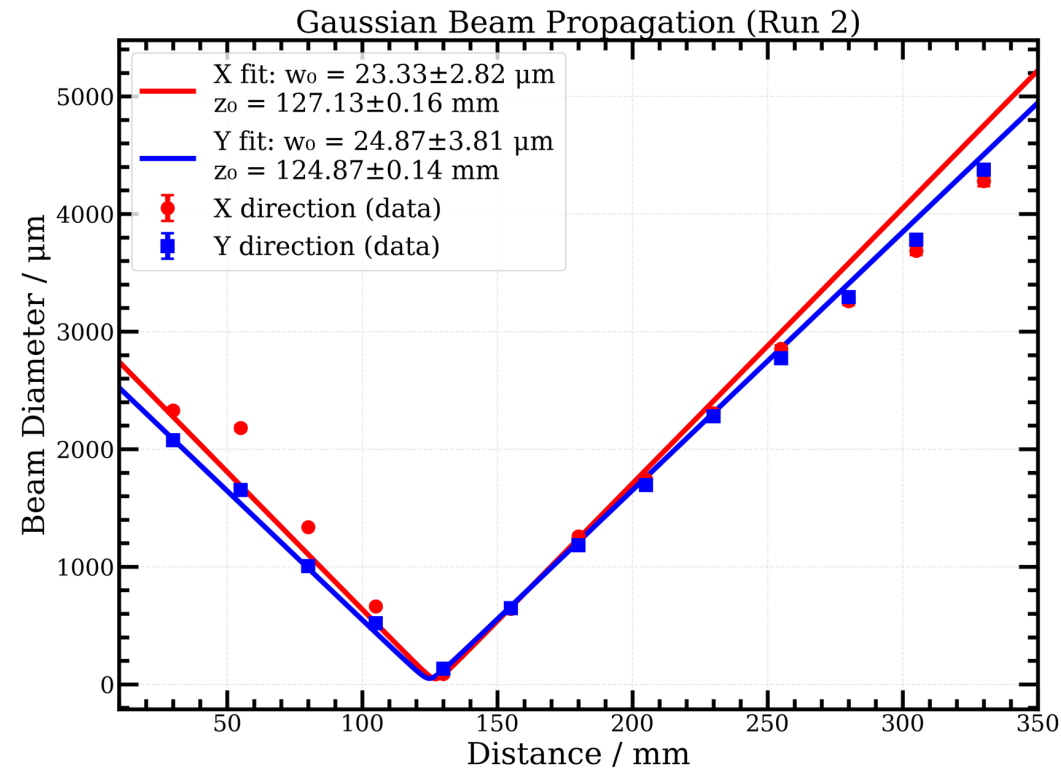
Particam Laser Spot Movement

- Conversion: 1px = 2 μm
- The centroid y-position = stage x-position due to the orientation of the sensor.
- Stage step size = 10 μm .
- Fit: $m = 0.495 \times 2 = 0.99$

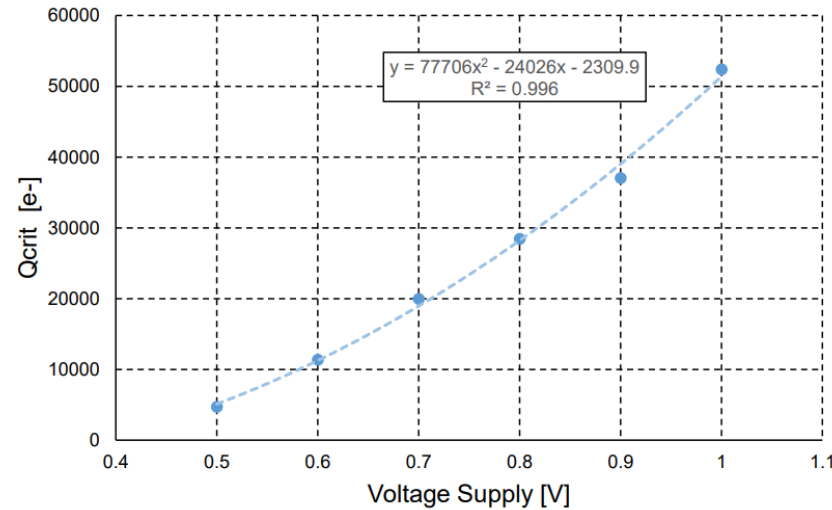
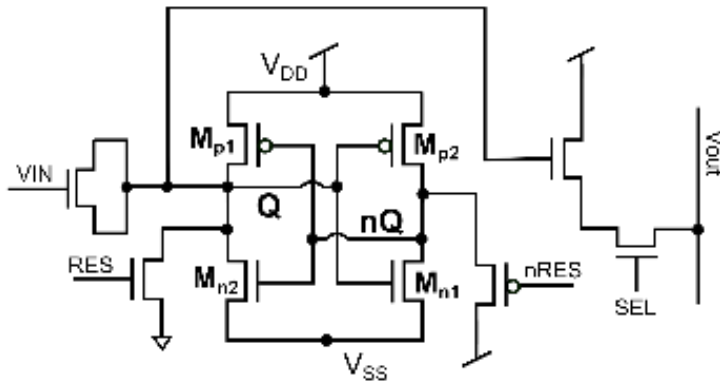


Beam Profiling

- A beam profiler was used to determine the size of the beam waist.
- Plots for two of the runs.



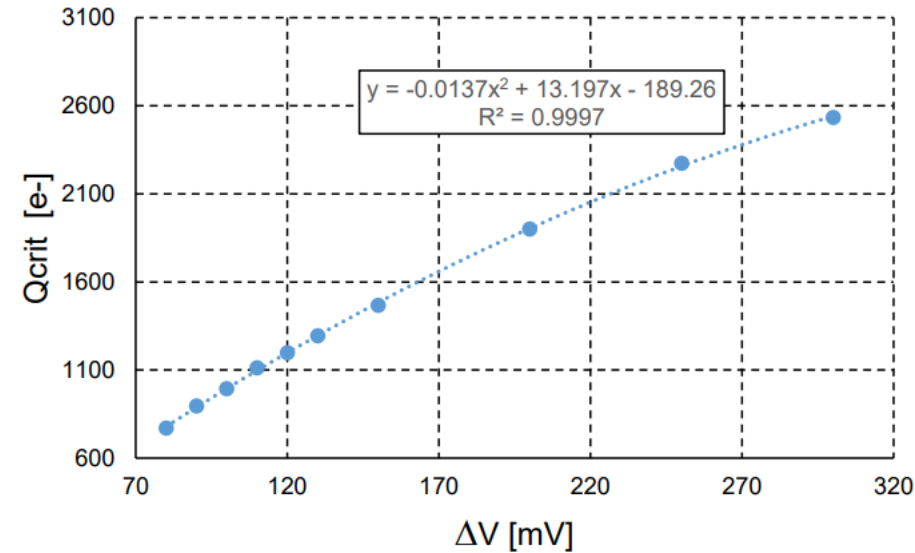
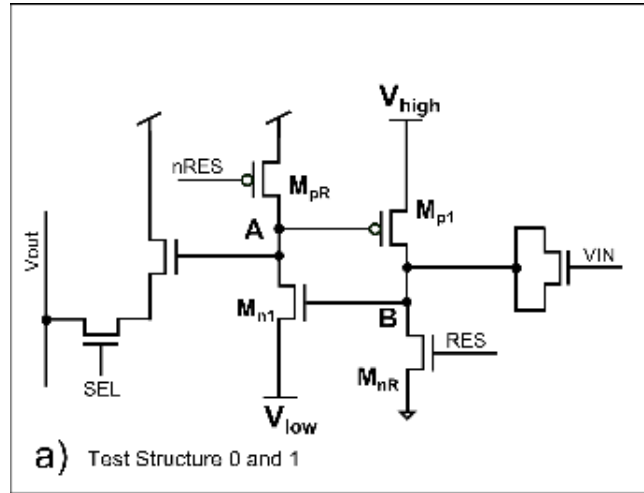
Experimental results: standard Array



Test structure allows us to have an estimation of the minimum charge needed for changing the memory state

As expected Q_T reduces as the pixel voltage supply reduces, $Q_T \sim 5 \text{ ke}^-$ working @ 0.5V $\rightarrow$ impact on the readout system.

Experimental results: custom array

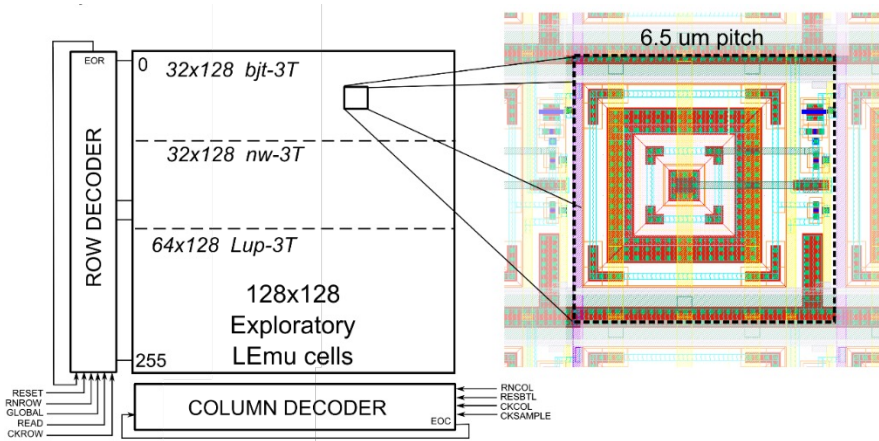


Q_T depends on DV and not any more on V_{dd} . DV is the difference between V_{low} and gnd (equal to $V_{dd} - V_{high}$)

Test structure shows a minimum Q_T lower than $1ke^-$

Not sensitive to a-particle. Not tested with laser.

“Exploratory” layout



Definition of three different pixels:

1. photo-transistor (3T pixel structure);
2. nwell junction (3T pixel structure);
3. “latch-up” (weak positive feedback) pixel (3T pixel structure);

